



DMMT3906W

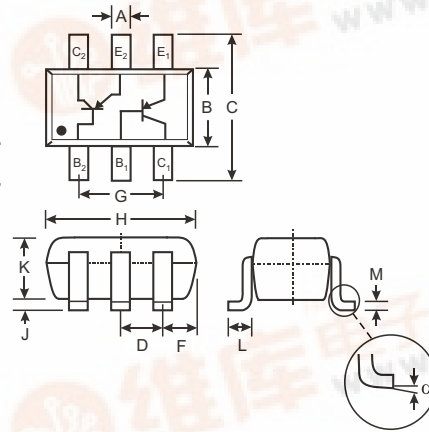
MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Intrinsically Matched PNP Pair (Note 1)
- Small Surface Mount Package
- 2% Matched Tolerance, h_{FE} , $V_{CE(SAT)}$, $V_{BE(SAT)}$
- Lead Free/RoHS Compliant (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Below): K4B
- Ordering & Date Code Information: See Below
- Weight: 0.015 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	0.10	
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
8°		
All Dimensions in mm		

Maximum Ratings @ $T_A = 25$ C unless otherwise specified

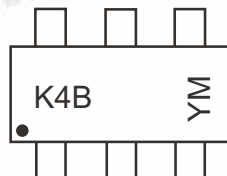
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Power Dissipation (Note 3)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 3)	R_{JA}	625	C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	C

Ordering Information (Note 4)

Device	Packaging	Shipping
DMMT3906W-7-F	SOT-363	3000/Tape & Reel

- Notes:
- Built with adjacent die from a single wafer.
 - No purposefully added lead.
 - Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 - For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K4B = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

Year Code	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	
Year Code	N	P	R	S	T	U	V	W	X	Y	Z	
Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Month Code	1	2	3	4	5	6	7	8	9	O	N	D



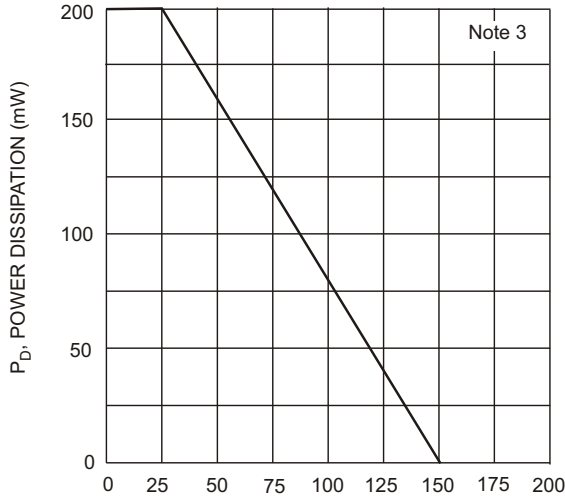


Electrical Characteristics @ $T_A = 25\text{ C}$ unless otherwise specified

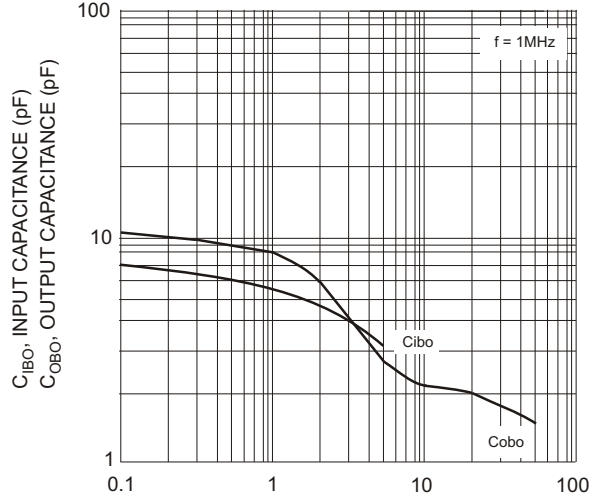
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		V	$I_C = -10\text{ A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	$I_E = -10\text{ A}, I_C = 0$
Collector Cutoff Current	I_{CEX}		-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
Base Cutoff Current	I_{BL}		-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
ON CHARACTERISTICS (Note 5)					
DC Current Gain (Note 6)	h_{FE}	60 80 100 60 30	300		$I_C = -100\mu\text{A}, V_{CE} = -1.0\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage (Note 6)	$V_{CE(SAT)}$		-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 6)	$V_{BE(SAT)}$	-0.65	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Voltage Matching	V_{BE}		-1	mV	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}		10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	2.0	12	k	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400		
Output Admittance	h_{oe}	3.0	60	S	
Current Gain-Bandwidth Product	f_T	250		MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF		4.0	dB	$V_{CE} = -5.0\text{V}, I_C = -100\text{ A}, R_S = 1.0\text{k} f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d		35	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}, V_{BE(off)} = 0.5\text{V}, I_{B1} = -1.0\text{mA}$
Rise Time	t_r		35	ns	
Storage Time	t_s		225	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}, I_{B1} = I_{B2} = -1.0\text{mA}$
Fall Time	t_f		75	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

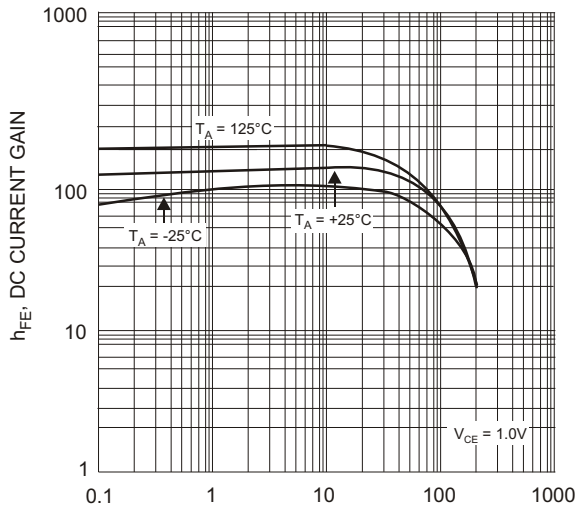
6. The DC current gain, h_{FE} , (matched at $I_C = -10\text{mA}$ and $V_{CE} = -1.0\text{V}$) Collector-Emitter Saturation Voltage, $V_{CE(sat)}$, and Base-Emitter Saturation Voltage, $V_{BE(sat)}$ are matched with typical matched tolerances of 1% and maximum of 2%.



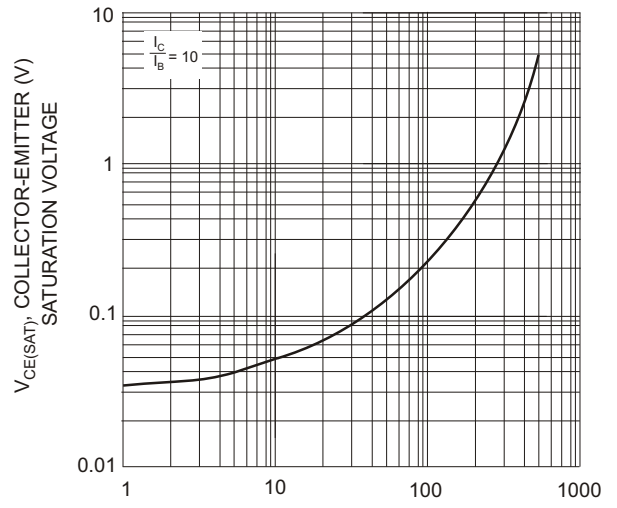
T_A, AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs Ambient Temperature



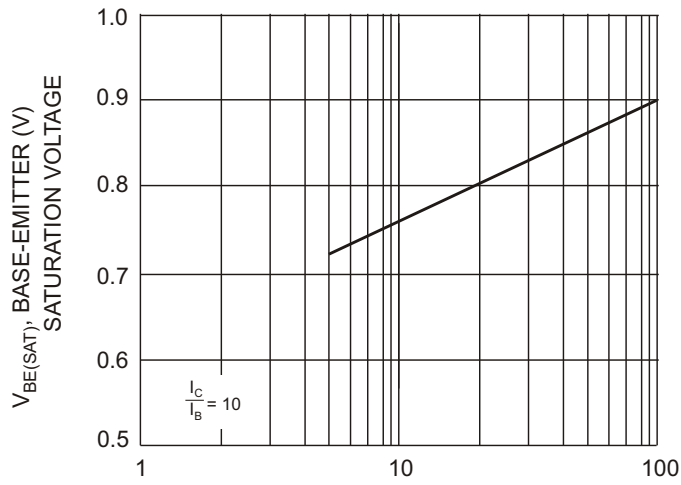
V_{CB}, COLLECTOR-BASE VOLTAGE (V)
Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



I_C, COLLECTOR CURRENT (mA)
Fig. 3, Typical DC Current Gain vs Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



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